

SHINDENGEN

3 Phase Bridge Diode

Diode Module

S10VTA80

800V 10A

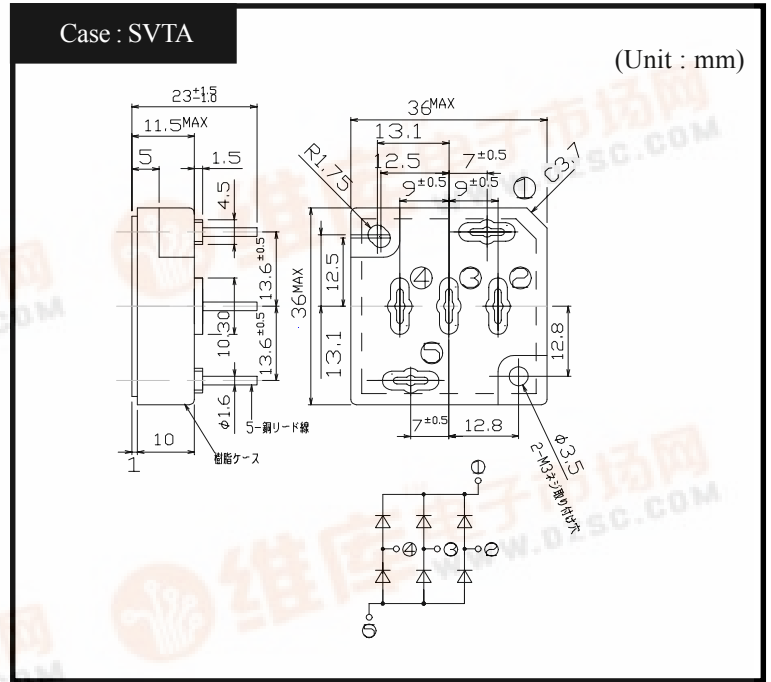
FEATURES

- Dual In-Line Package
- Compact 3 phase bridge
- High IFSM
- Applicable to mount on glass-epoxy substrate (VTA type)

APPLICATION

- Big Power Supply
- Air conditioner
- Factory Automation, Inverter

OUTLINE DIMENSIONS



RATINGS

- Absolute Maximum Ratings (If not specified Tc=25°C)

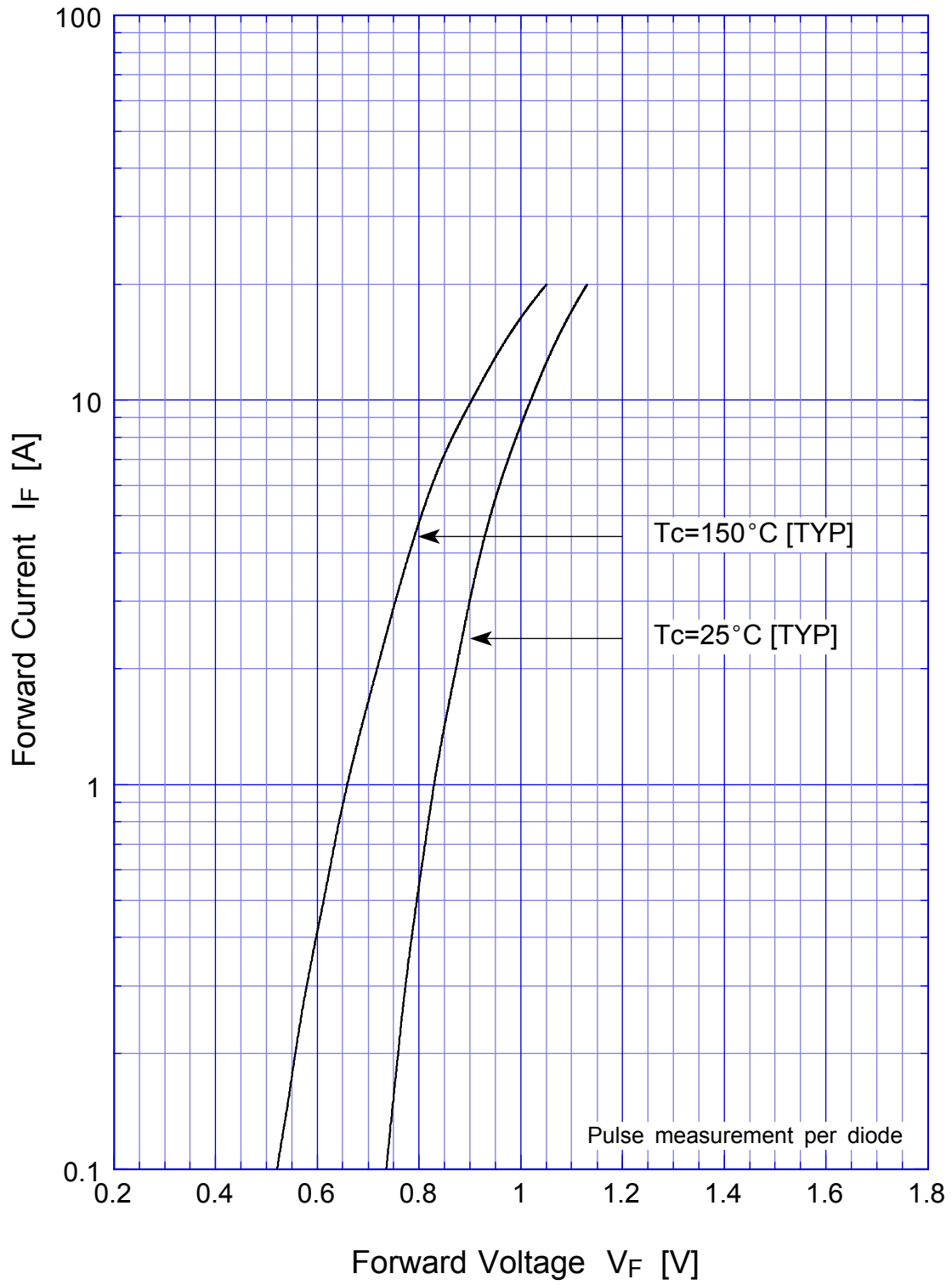
Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	Tstg		-40~150	°C
Operating Junction Temperature	Tj		150	°C
Maximum Reverse Voltage	V _{RM}		800	V
Average Rectified Forward Current	I _O	50Hz sine wave, R-load With heatsink Tc=137°C	10	A
Peak Surge Forward Current	I _{FSM}	50Hz sine wave, Non-repetitive 1cycle peak value, Rating of per diode Tj=25°C	150	A
Current Squared Time	I ² t	1ms ≤ t < 10ms Tc=25°C	80	A ² s
Dielectric Strength	Vdis	Terminals to case, AC 1 minute	2	kV
Mounting Torque	TOR	(Recommended torque : 0.6N·m)	0.8	N·m

- Electrical Characteristics (If not specified Tc=25°C)

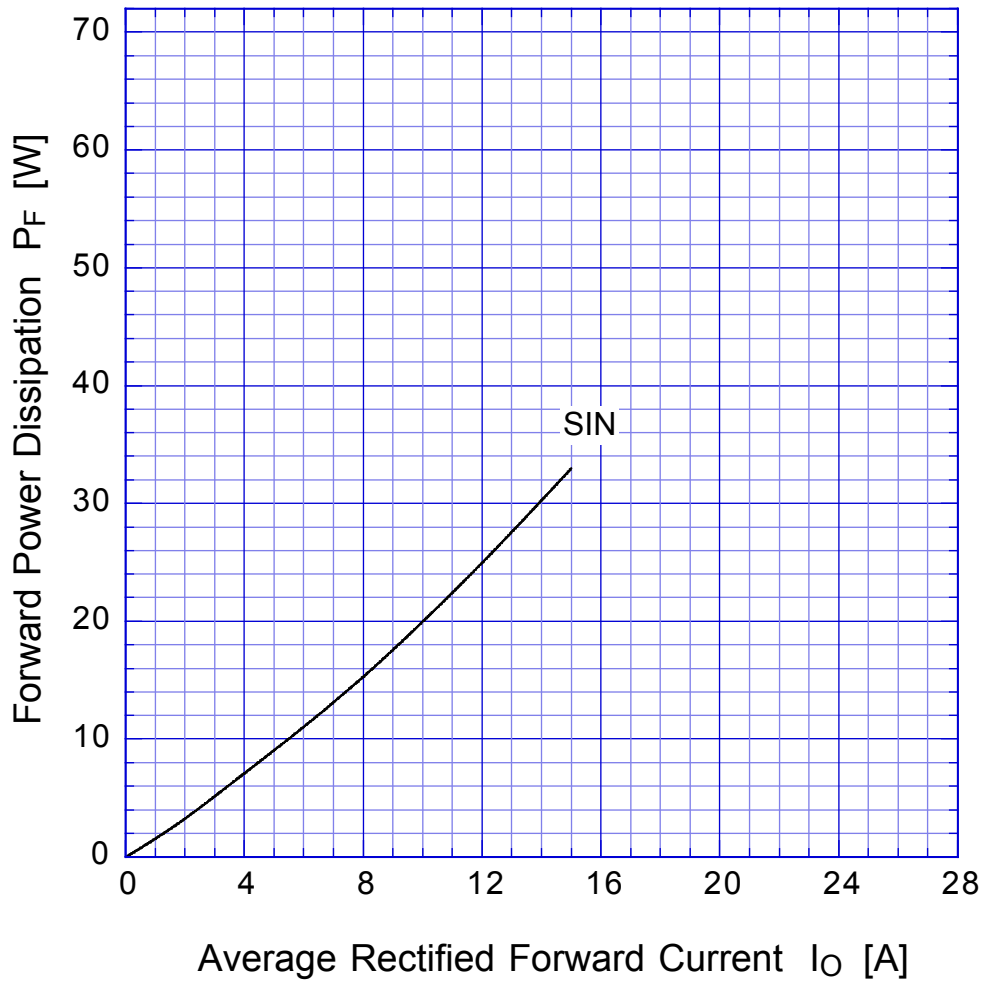
Item	Symbol	Conditions	Ratings	Unit
Forward Voltage	V _F	IF=3.5A, Pulse measurement, Rating of per diode	Max.1.05	V
Reverse Current	I _R	V _R =V _{RM} , Pulse measurement, Rating of per diode	Max.10	μA
Thermal Resistance	θ _{jc}	junction to case	Max.0.65	°C/W



S10VTA80 Forward Voltage



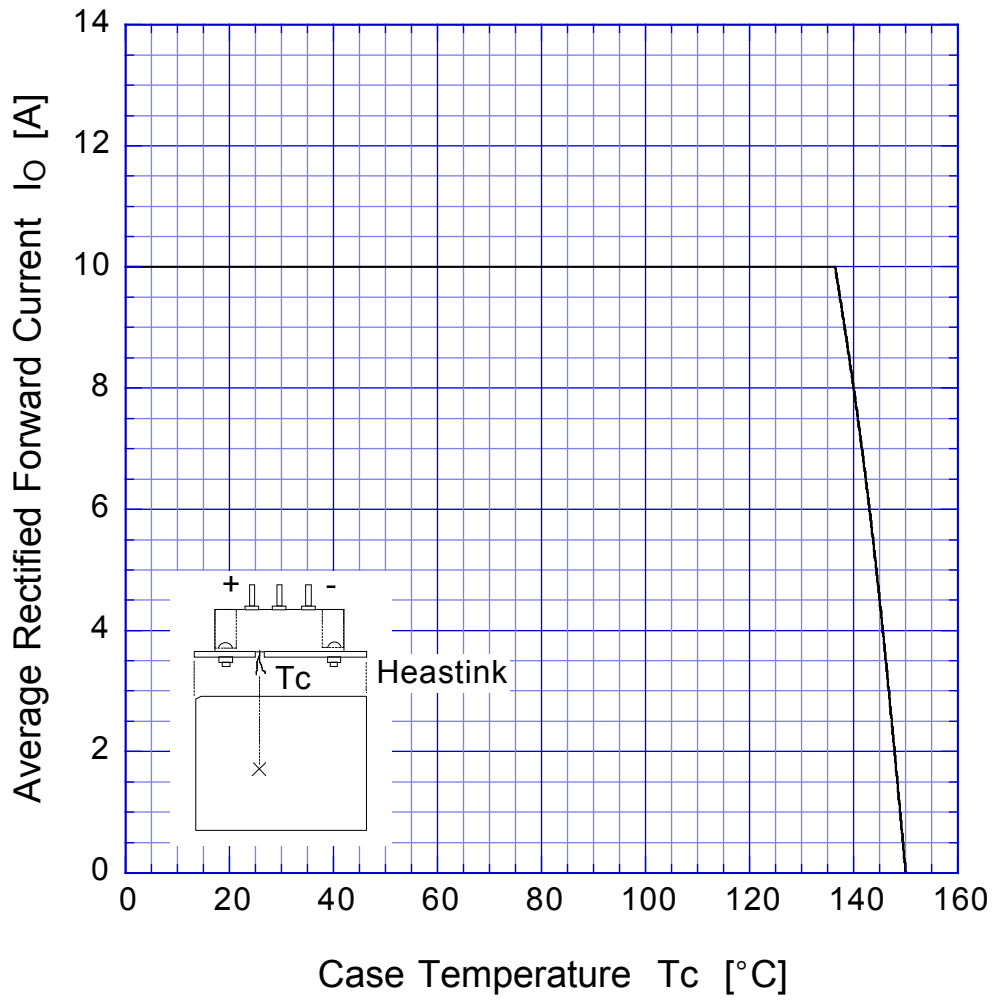
S10VTA80 Forward Power Dissipation



$T_j = 150^\circ\text{C}$
Sine wave

S10VTA80

Derating Curve



Sine wave
R-load
with heatsink

S10VTA80 Peak Surge Forward Capability

